Kazushige Ueda

List of Publications by Year
in descending order

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122	9,195	50170	38300
papers	citations	46 h-index	95 g-index

127	127	127	6653
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Thin-Film Transistor Fabricated in Single-Crystalline Transparent Oxide Semiconductor. Science, 2003, 300, 1269-1272.	6.0	1,709
2	Transparent p-Type Conducting Oxides: Design and Fabrication of p-n Heterojunctions. MRS Bulletin, 2000, 25, 28-36.	1.7	530
3	Electronic structure and optoelectronic properties of transparent p-type conducting CuAlO[sub 2]. Journal of Applied Physics, 2000, 88, 4159.	1.1	413
4	Epitaxial growth of transparent p-type conducting CuGaO[sub 2] thin films on sapphire (001) substrates by pulsed laser deposition. Journal of Applied Physics, 2001, 89, 1790.	1.1	390
5	Bipolarity in electrical conduction of transparent oxide semiconductor CuInO2 with delafossite structure. Applied Physics Letters, 2001, 78, 1583-1585.	1.5	332
6	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides MCuOCh (M = Bi, La; Ch = S, Se, Te): Effects of Electronic Configurations of M³⁺ Ions. Chemistry of Materials, 2008, 20, 326-334.	3.2	258
7	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO3(ZnO)5 films. Applied Physics Letters, 2004, 85, 1993-1995.	1.5	247
8	New ultravioletâ€transport electroconductive oxide, ZnGa2O4spinel. Applied Physics Letters, 1994, 64, 1077-1078.	1.5	214
9	Fabrication of transparent pâ€“n heterojunction thin film diodes based entirely on oxide semiconductors. Applied Physics Letters, 1999, 75, 2851-2853.	1.5	194
10	Single-Crystalline Films of the Homologous Series InGaO3(ZnO)m Grown by Reactive Solid-Phase Epitaxy. Advanced Functional Materials, 2003, 13, 139-144.	7.8	179
11	Degenerate p-type conductivity in wide-gap LaCuOS1âˆ’xSex (x=0â€“1) epitaxial films. Applied Physics Letters, 2003, 82, 1048-1050.	1.5	166
12	Frontier of transparent conductive oxide thin films. Vacuum, 2002, 66, 419-425.	1.6	164
13	A p-Type Amorphous Oxide Semiconductor and Room Temperature Fabrication of Amorphous Oxide pâ€“n Heterojunction Diodes. Advanced Materials, 2003, 15, 1409-1413.	11.1	154
14	Fabrication of all oxide transparent pâ€“n homojunction using bipolar CuInO2 semiconducting oxide with delafossite structure. Solid State Communications, 2001, 121, 15-17.	0.9	134
15	Room-temperature excitons in wide-gap layered-oxysulfide semiconductor: LaCuOS. Applied Physics Letters, 2001, 78, 2333-2335.	1.5	133
16	Frontier of transparent oxide semiconductors. Solid-State Electronics, 2003, 47, 2261-2267.	0.8	129
17	New oxide phase with wide band gap and high electroconductivity, MgIn2O4. Applied Physics Letters, 1992, 61, 1954-1955.	1.5	128
18	Crystal structure of metastable Îº-CeZrO4 phase possessing an ordered arrangement of Ce and Zr ions. Journal of Alloys and Compounds, 2000, 312, 94-103.	2.8	124

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19	Transparent Conducting Oxides Based on the Spinel Structure. Journal of the American Ceramic Society, 1999, 82, 3330-3336.	1.9	115
20	Electronic structure of the transparentp-type semiconductor (LaO)CuS. Physical Review B, 2001, 64, .	1.1	114
21	Decomposition of water by a CaTiO3 photocatalyst under UV light irradiation. Materials Research Bulletin, 2002, 37, 2401-2406.	2.7	112
22	Heteroepitaxial growth of a wide-gap p-type semiconductor, LaCuOS. Applied Physics Letters, 2002, 81, 598-600.	1.5	105
23	ZnRh2O4: A p-type semiconducting oxide with a valence band composed of a low spin state of Rh3+ in a 4d6 configuration. Applied Physics Letters, 2002, 80, 1207-1209.	1.5	105
24	Band gap engineering, band edge emission, and p-type conductivity in wide-gap LaCuOS1â^'xSex oxychalcogenides. Journal of Applied Physics, 2002, 91, 4768-4770.	1.1	102
25	Lowâ€Drivingâ€Voltage Electroluminescence in Perovskite Films. Advanced Materials, 2009, 21, 3699-3702.	11.1	98
26	Single-atomic-layered quantum wells built in wide-gap semiconductorsLnCuOCh(Ln=lanthanide,Ch=chalcogen). Physical Review B, 2004, 69, .	1.1	97
27	Electrical and Optical Properties and Electronic Structures of LnCuOS (Ln = Laâ^¼Nd). Chemistry of Materials, 2003, 15, 3692-3695.	3.2	94
28	Heavy hole doping of epitaxial thin films of a wide gap p-type semiconductor, LaCuOSe, and analysis of the effective mass. Applied Physics Letters, 2007, 91, .	1.5	91
29	Wide-gap layered oxychalcogenide semiconductors: Materials, electronic structures and optoelectronic properties. Thin Solid Films, 2006, 496, 8-15.	0.8	86
30	New oxide phase with wide band gap and high electroconductivity CdGa2O4spinel. Applied Physics Letters, 1993, 62, 499-500.	1.5	79
31	Intrinsic excitonic photoluminescence and band-gap engineering of wide-gapp-type oxychalcogenide epitaxial films of LnCuOCh (Ln=La, Pr, and Nd; Ch=S or Se) semiconductor alloys. Journal of Applied Physics, 2003, 94, 5805-5808.	1.1	79
32	Preparation of transparent p-type (La1â^'xSrxO)CuS thin films by r.f. sputtering technique. Thin Solid Films, 2002, 411, 125-128.	0.8	77
33	n-type electrical conduction in transparent thin films of delafossite-type AgInO2. Applied Physics Letters, 1998, 72, 1036-1038.	1.5	73
34	Blue photoluminescence in Ti-doped alkaline-earth stannates. Journal of Solid State Chemistry, 2007, 180, 1410-1413.	1.4	68
35	Electronic structure and optical properties of SrCu2O2. Journal of Applied Physics, 2002, 91, 3074-3078.	1.1	66
36	Electrical conductivity control in transparent p-type (LaO)CuS thin films prepared by rf sputtering. Journal of Applied Physics, 2002, 91, 9177-9181.	1.1	65

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37	Energy band structure of LaCuOCh (Ch = S, Se and Te) calculated by the full-potential linearized augmented plane-wave method. Journal of Physics Condensed Matter, 2004, 16, 5179-5186.	0.7	65
38	Vacuum ultraviolet reflectance and electron energy loss spectra of. Journal of Physics Condensed Matter, 1998, 10, 3669-3677.	0.7	58
39	Growth mechanism for single-crystalline thin film of InGaO3(ZnO)5 by reactive solid-phase epitaxy. Journal of Applied Physics, 2004, 95, 5532-5539.	1.1	58
40	Electrical Properties and Structure of p-Type Amorphous Oxide SemiconductorxZnOÂ·Rh2O3. Advanced Functional Materials, 2005, 15, 968-974.	7.8	58
41	Green, Orange, and Magenta Luminescence in Strontium Stannates with Perovskite-Related Structures. Japanese Journal of Applied Physics, 2006, 45, 6981-6983.	0.8	57
42	Third-order optical nonlinearity originating from room-temperature exciton in layered compounds LaCuOS and LaCuOSe. Applied Physics Letters, 2004, 84, 879-881.	1.5	56
43	Tricolor luminescence in rare earth doped CaZrO3 perovskite oxides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 100-103.	1.7	56
44	Mechanism for Heteroepitaxial Growth of Transparent P-Type Semiconductor:â€‰ LaCuOS by Reactive Solid-Phase Epitaxy. Crystal Growth and Design, 2004, 4, 301-307.	1.4	54
45	Excitonic blue luminescence from p-LaCuOSeâˆ•n-InGaZn5O8 light-emitting diode at room temperature. Applied Physics Letters, 2005, 87, 211107.	1.5	53
46	Opto-electronic properties and light-emitting device application of widegap layered oxychalcogenides: LaCuOCh(Ch= chalcogen) and La2CdO2Se2. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2800-2811.	0.8	50
47	Preparation and crystal structure analysis of CeCuOS. Journal of Solid State Chemistry, 2003, 170, 182-187.	1.4	46
48	Field-Induced Current Modulation in Nanoporous Semiconductor, Electron-Doped 12CaOÂ·7Al2O3. Chemistry of Materials, 2005, 17, 6311-6316.	3.2	45
49	Red photoluminescence in praseodymium-doped titanate perovskite films epitaxially grown by pulsed laser deposition. Applied Physics Letters, 2006, 89, 261915.	1.5	45
50	Crystal structure of LaCuOS1âˆ’xSex oxychalcogenides. Thin Solid Films, 2002, 411, 115-118.	0.8	44
51	High-temperature thermoelectric properties of La-doped BaSnO3 ceramics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 29-32.	1.7	44
52	Electrical and Optical Properties of Layered Oxysulfides with CuS Layers: Srâˆ’Cuâˆ’Mâˆ’Oâˆ’S System (M =) Tj ETQq0 0 0 rgBT /Overlock	3.2	41
53	Wide gap p-type degenerate semiconductor: Mg-doped LaCuOSe. Thin Solid Films, 2003, 445, 304-308.	0.8	41
54	Photoluminescence properties of Pr doped and Tbâ€“Mg codoped CaSnO3 with perovskite structure. Thin Solid Films, 2008, 516, 5885-5889.	0.8	41

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55	Site-Selective Doping and Site-Sensitive Photoluminescence of Eu³⁺ and Tb³⁺ in Perovskite-Type LaLuO₃. Inorganic Chemistry, 2019, 58, 10890-10897.	1.9	40
56	Novel film growth technique of single crystalline In2O3(ZnO)m (m=integer) homologous compound. Thin Solid Films, 2002, 411, 147-151.	0.8	39
57	Thermoelectric properties of layered oxyselenides La1â^'xSrxCuOSe (x=0 to 0.2). Journal of Applied Physics, 2004, 95, 3594-3597.	1.1	39
58	Valence-band structures of layered oxychalcogenides, LaCuOCh (Ch=S, Se, and Te), studied by ultraviolet photoemission spectroscopy and energy-band calculations. Journal of Applied Physics, 2005, 98, 043506.	1.1	39
59	Electronic Structure of Sr2Cu2ZnO2S2Layered Oxysulfide with CuS Layers. Chemistry of Materials, 2002, 14, 1037-1041.	3.2	36
60	Synthesis of single-phase layered oxychalcogenide La2CdO2Se2: crystal structure, optical and electrical properties. Journal of Materials Chemistry, 2004, 14, 2946.	6.7	35
61	Study on electronic structure of CaTiO3by spectroscopic measurements and energy band calculations. Journal of Physics Condensed Matter, 1999, 11, 3535-3545.	0.7	34
62	Optical Properties and Two-Dimensional Electronic Structure in Wide-Gap Layered Oxychalcogenide:â€‰ La2CdO2Se2. Journal of Physical Chemistry B, 2004, 108, 17344-17351.	1.2	33
63	Li-Doped NiO Epitaxial Thin Film with Atomically Flat Surface. Journal of Materials Research, 2004, 19, 913-920.	1.2	32
64	Fabrication of heteroepitaxial thin films of layered oxychalcogenides LnCuOCh (Ln = Laâ€“Nd; Ch =) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	1.2	31
65	Photoluminescence from Epitaxial Films of Perovskite-type Alkaline-earth Stannates. Applied Physics Express, 2008, 1, 015003.	1.1	29
66	Electrical and magnetic properties of hole-dopedSr1+xLa1â^'xFeO4. Physical Review B, 1994, 49, 10194-10199.	1.1	28
67	Fabrication of Tbâ€“Mg codoped CaSnO3 perovskite thin films and electroluminescence devices. Thin Solid Films, 2010, 518, 3063-3066.	0.8	28
68	Thermoelectric properties and figure of merit of perovskite-type Ba1â^'xLaxSnO3 with x=0.002â€“0.008. Solid State Communications, 2013, 172, 49-53.	0.9	28
69	Preparation of n-type conductive transparent thin films of AgInO2:Sn with delafossite-type structure by pulsed laser deposition. Journal of Applied Physics, 2000, 88, 3067-3069.	1.1	27
70	Carrier generation in highly oriented WO3 films by proton or helium implantation. Journal of Applied Physics, 2002, 92, 2017-2022.	1.1	27
71	Electrical and Photonic Functions Originating from Low-Dimensional Structures in Wide-Gap Semiconductors LnCuOCh (Ln=lanthanide, Ch=chalcogen): A Review. Journal of the Ceramic Society of Japan, 2005, 113, 10-16.	1.3	24
72	All oxide transparent MISFET using high-k dielectrics gates. Microelectronic Engineering, 2004, 72, 294-298.	1.1	22

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73	Two-dimensional electronic structure and multiple excitonic states in layered oxychalcogenide semiconductors, LaCuOCh (Ch=S, Se, Te): Optical properties and relativistic ab initio study. Thin Solid Films, 2005, 486, 98-103.	0.8	21
74	Layered mixed-anion compounds: Epitaxial growth, active function exploration, and device application. Journal of the European Ceramic Society, 2009, 29, 245-253.	2.8	21
75	Synthesis of Pr3+ doped or Tb3+â€“Mg codoped CaSnO3 perovskite phosphor by the polymerized complex method. Journal of Sol-Gel Science and Technology, 2012, 61, 362-366.	1.1	21
76	Luminescence and Valence of Tb Ions in Alkaline Earth Stannates and Zirconates Examined by X-ray Absorption Fine Structures. Inorganic Chemistry, 2017, 56, 12625-12630.	1.9	21
77	Luminescence and Location of Gd³⁺ or Tb³⁺ Ions in Perovskite-Type LaScO₃. Inorganic Chemistry, 2018, 57, 8718-8721.	1.9	20
78	Optoelectronic properties and electronic structure of YCuOSe. Journal of Applied Physics, 2007, 102, 113714.	1.1	19
79	UV emission from Gd3+ ions in Gd3+â€“Pr3+ codoped YAlO3 perovskite. Journal of Luminescence, 2013, 141, 44-47.	1.5	19
80	Phase formation and UV luminescence of Gd3+ doped perovskite-type YScO3. Journal of Solid State Chemistry, 2016, 242, 170-174.	1.4	18
81	Natural nanostructures in ionic semiconductors. Microelectronic Engineering, 2004, 73-74, 620-626.	1.1	17
82	Quantum beat between two excitonic levels split by spinâ€“orbit interactions in the oxychalcogenide LaCuOS. Optics Letters, 2004, 29, 1659.	1.7	17
83	Transparent Conductive Oxides. Springer Handbooks, 2017, , 1-1.	0.3	17
84	Electrical properties and local structure ofn-type conducting amorphous indium sulphide. Philosophical Magazine Letters, 2004, 84, 665-671.	0.5	16
85	Synthesis of Pb(Mg_{1/3}Nb_{2/3})O₃ Powder by the Spray Pyrolysis with Ultrasonic Atomizer. Journal of the Ceramic Society of Japan, 1992, 100, 246-249.	1.3	15
86	EPITAXIAL GROWTH OF TRANSPARENT CONDUCTIVE OXIDES. International Journal of Modern Physics B, 2002, 16, 173-180.	1.0	15
87	Single crystal growth of LaCuOS by the flux method. Journal of Crystal Growth, 2008, 311, 114-117.	0.7	15
88	Photoluminescence excitation spectra of lanthanide doped YAlO 3 in vacuum ultraviolet region. Optical Materials, 2017, 66, 327-331.	1.7	15
89	Photo- and cathodoluminescence of Eu3+ or Tb3+ doped CaZrO3 films prepared by pulsed laser deposition. Optical Materials, 2017, 73, 504-508.	1.7	15
90	Excitonic properties related to valence band levels split by spinâ€“orbit interaction in layered oxychalcogenide LaCuOCh(Ch=S,Se). Journal of Luminescence, 2005, 112, 66-70.	1.5	14

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91	UV cathodoluminescence of Gd³⁺doped and Gd³⁺ï£¿Pr³⁺co-doped YAlO₃epitaxial thin films. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 703-706.	0.8	14
92	Site-Dependent Eu3+ Photoluminescence in Double Perovskite-Type Alkaline Earth Lanthanum Tantalates. Journal of Luminescence, 2021, 229, 117683.	1.5	14
93	Thermoelectric properties of delafossite-type layered oxides AgIn1â^'xSnxO2. Journal of Applied Physics, 2005, 98, 013706.	1.1	13
94	UV emissions in Gd3+ doped or Gd3+â€“Pr3+ Co-doped IIIâ€“III perovskite-type RMO3 (R=Y, La; M=Al, Ga). Thin Solid Films, 2014, 559, 23-26.	0.8	12
95	Preparation of thin films of perovskite-type YAlO 3 :Gd 3+ â€“Pr 3+ UV phosphors. Thin Solid Films, 2014, 571, 90-93.	0.8	12
96	Site Dependence of Tb3+ Luminescence in Double Perovskite-Type Alkaline Earth Lanthanum Tantalates. Journal of Physical Chemistry C, 2020, 124, 854-860.	1.5	12
97	Electron transport in InGaO3(ZnO)m (m=integer) studied using single-crystalline thin films and transparent MISFETs. Thin Solid Films, 2003, 445, 322-326.	0.8	11
98	Lanthanide 4f energy levels in perovskite-type YAlO3. Journal of Luminescence, 2015, 168, 14-19.	1.5	10
99	Electronic structure of hole-dopedSr1+xLa1â^'xFeO4studied by UPS and XAS. Physical Review B, 1994, 49, 10200-10205.	1.1	9
100	Transparent p- and n-Type Conductive Oxides With Delafossite Structure. Materials Research Society Symposia Proceedings, 2000, 623, 235.	0.1	8
101	Origin of highâ€density hole doping and anisotropic hole transport in a wide gap layered semiconductor LaCuOSe studied by firstâ€principles calculations. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1636-1641.	0.8	8
102	Carrier doping into MgIn2O4 epitaxial thin films by proton implantation. Journal of Applied Physics, 2002, 91, 2112-2117.	1.1	7
103	Determination of 4f energy levels for trivalent lanthanide ions in YAlO3 by X-ray photoelectron spectroscopy. Thin Solid Films, 2016, 614, 69-72.	0.8	6
104	Site-Dependent Tb³⁺ Luminescence by Energy Transfer from Ce³⁺ in Ce³⁺â€“Tb³⁺ Codoped LaLuO₃. Journal of Physical Chemistry C, 2022, 126, 6499-6504.	1.5	6
105	Thermoelectric properties and figure of merit of perovskite-type Sr1â^'xLaxSnO3 ceramics. Ceramics International, 2017, 43, 9653-9657.	2.3	5
106	Thermoelectric Properties of P -Type BaSnO3 Ceramics Doped with Cobalt. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2011, 58, 149-154.	0.1	4
107	Ultraviolet emission from YAlO3:Gd3+ thin film electroluminescent devices fabricated on perovskite-type oxide substrates. Optical Materials, 2019, 91, 371-375.	1.7	3
108	Ln³⁺ 4f Energy Levels in CaTiO₃ Analyzed by XPS Measurements. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700776.	0.8	3

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109	X-ray Amorphous P-type Conductive Oxide; ZnRh2O4. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	2
110	Two-Dimensional Electronic Structures in Layered Oxychalcogenide Semiconductors, LaCuOCh (Ch=S,) Tj ETQq0 0 0 rgBT /Overlock 10	0.1	2
111	Optical and electrical properties of heat-resistant Sb-doped Sn1â^'xHfxO2 transparent conducting films. Thin Solid Films, 2012, 520, 3755-3759.	0.8	2
112	Energy Diagrams of Lanthanide Energy Levels in Perovskiteâ€Type Calciumâ€Based Double Oxides Examined by Xâ€ray Photoelectron Spectroscopy. Physica Status Solidi (B): Basic Research, 0, , 2100450.	0.7	2
113	Host Lattice-Excitation-Enhanced Photoluminescence in Eu³⁺-Doped LaInO₃ Epitaxial Films. Crystal Growth and Design, 2021, 21, 2663-2667.	1.4	1
114	High-Temperature Thermoelectric Properties of La-Doped Ba1-xSrxSnO3 Ceramics. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2009, 56, 555-560.	0.1	1
115	Electronic Structure of SrNb8O14 and Mg3Nb6O11 Studied by Spectroscopic Methods. Chemistry of Materials, 2000, 12, 2659-2663.	3.2	0
116	Bipolar Electrical Conductive Transparent Oxide, CuInO2. Materials Research Society Symposia Proceedings, 2001, 666, 3141.	0.1	0
117	Transparent P-type Conducting LaCuOS Layered Oxysulfide. Materials Research Society Symposia Proceedings, 2001, 666, 271.	0.1	0
118	Wide-gap P-type Conductive Properties in Layered Oxychalcogenides. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0
119	Heteroepitaxial Growth of a Wide Gap P-type Oxysulfide, LaCuOS. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0
120	Carrier transport of extended and localized states in InGaO3(ZnO)5. Materials Research Society Symposia Proceedings, 2004, 811, 90.	0.1	0
121	Optical Properties and Two-Dimensional Electronic Structure in Wide-Gap Layered Oxychalcogenide: La2CdO2Se2.. ChemInform, 2005, 36, no.	0.1	0
122	Electrical and Photonic Functions Originating from Low-Dimensional Structures in Wide-Gap Semiconductors LnCuOCh (Ln: Lanthanide, Ch: Chalcogen): A Review. ChemInform, 2005, 36, no.	0.1	0